

ON Semiconductor®

FGY120T65SPD-F085 650V, 120A Field Stop Trench IGBT With Soft Fast Recovery Diode

Features

- · AEC-Q101 Qualified
- Very low saturation voltage : $V_{CE(sat)} = 1.5 V(Typ.) @ I_C =$ 120 A
- Maximum junction temperature : T_{.1} = 175 °C
- · Positive temperature Co-efficient
- · Tight parameter distribution
- · High input impedance
- 100% of the parts are dynamically tested
- Short circuit ruggedness > 6 μs @ 25 °C
- · Copacked with soft, fast recovery Extremefast diode

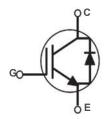
Benefits

- Very Low conduction and switching losses for a high efficiency operation in various applications
- · Rugged transient reliability
- Outstanding parallel operation performance with balance current sharing
- Low EMI

Applications

- · Traction inverter for HEV/EV
- Auxiliary DC/AC converter
- Motor drives
- · Other power-train applications requiring high power switch





Absolute Maximum Ratings

Symbol	Description		Ratings	Units
V _{CES}	Collector to Emitter Voltage		650	V
V _{GES}	Gate to Emitter Voltage		± 20	V
	Transient Gate to Emitter Voltage		± 30	V
Ic	Collector Current (Note1)	@ T _C = 25 °C	240	А
	Collector Current	@ T _C = 100 °C	220	А
I _{Nominal}	Nominal Current		120	А
I _{CM}	Pulsed Collector Current		378	А
I _F	Diode Forward Current (Note1)	@ T _C = 25 °C	240	А
	Diode Forward Current	@ T _C = 100 °C	188	А
P _D	Maximum Power Dissipation	@ T _C = 25 °C	882	W
	Maximum Power Dissipation	@ T _C = 100 °C	441	W
SCWT	Short Circuit Withstand Time	@ T _C = 25 °C	6	μs
dV/dt	Voltage Transient Ruggedness (Note2)		10	V/ns
TJ	Operating Junction Temperature		-55 to +175	°C
T _{stg}	Storage Temperature Range		-55 to +175	°C
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	;	300	°C

- 1: Limited by bondwire 2: V_{CC} = 400 V, V_{GE} = 15 V, I_{CE} = 378 A, Inductive Load